

• General Description

The ZM930P06T combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for load switch and battery protection applications.

• Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

• Application

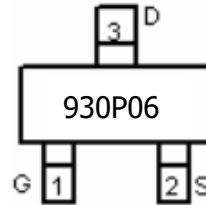
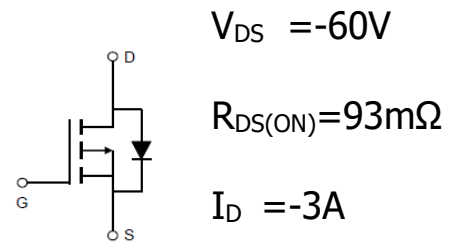
- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

• Ordering Information:

| | |
|---------------------------|-----------|
| Part NO. | ZM930P06T |
| Marking | 930P06 |
| Packing Information | REEL TAPE |
| Basic ordering unit (pcs) | 3000 |

• Absolute Maximum Ratings ($T_c = 25^\circ\text{C}$)

| Parameter | Symbol | Rating | Unit |
|---|----------------------------|------------|------------------|
| Drain-Source Voltage | V_{DS} | -60 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | V |
| Continuous Drain Current | $I_D@TC=25^\circ\text{C}$ | -3 | A |
| | $I_D@TC=75^\circ\text{C}$ | -2.3 | A |
| | $I_D@TC=100^\circ\text{C}$ | -1.9 | A |
| Pulsed Drain Current ^① | I_{DM} | -6 | A |
| Total Power Dissipation ^② | P_D | 1.5 | W |
| Total Power Dissipation($T_A=25^\circ\text{C}$) | $P_D@T_A=25^\circ\text{C}$ | 0.7 | W |
| Operating Junction Temperature | T_J | -55 to 150 | $^\circ\text{C}$ |
| Storage Temperature | T_{STG} | -55 to 150 | $^\circ\text{C}$ |
| Single Pulse Avalanche Energy | E_{AS} | 30 | mJ |

• Product Summary


SOT23-3



•Thermal resistance

| Parameter | Symbol | Min. | Typ. | Max. | Unit |
|--|-------------------|------|------|------|-------|
| Thermal resistance, junction - case ^② | R _{thJC} | - | - | 80 | ° C/W |
| Thermal resistance, junction - ambient | R _{thJA} | - | - | 180 | ° C/W |
| Soldering temperature, wavesoldering for 10s | T _{sold} | - | - | 265 | ° C |

•Electronic Characteristics

| Parameter | Symbol | Condition | Min. | Typ | Max. | Unit |
|-----------------------------------|---------------------|---|------|-----|------|------|
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} = 0V, I _D = -250uA | -60 | | | V |
| Gate Threshold Voltage | V _{GS(TH)} | V _{GS} = V _{DS} , I _D = -250uA | -1.2 | | -2.5 | V |
| Drain-Source Leakage Current | I _{DSS} | V _{DS} = -60V, V _{GS} = 0V | | | 1.0 | uA |
| Gate- Source Leakage Current | I _{GSS} | V _{GS} = ±20V, V _{DS} = 0V | | | ±100 | nA |
| Static Drain-source On Resistance | R _{DS(ON)} | V _{GS} = -10V, I _D = -3A | | 93 | 120 | mΩ |
| | | V _{GS} = -4.5V, I _D = -2A | | 128 | 166 | mΩ |
| Forward Transconductance | g _{FS} | V _{DS} = -10V, I _D = -2A | | 10 | | s |
| Source-drain voltage | V _{SD} | I _S = -3A | | | 1.28 | V |

•Electronic Characteristics

| Parameter | Symbol | Condition | Min. | Typ | Max. | Unit |
|------------------------------|------------------|-----------|------|-----|------|------|
| Input capacitance | C _{iss} | f = 1MHz | - | 650 | - | pF |
| Output capacitance | C _{oss} | | - | 120 | - | |
| Reverse transfer capacitance | C _{rss} | | - | 70 | - | |

•Gate Charge characteristics(T_a = 25°C)

| Parameter | Symbol | Condition | Min. | Typ | Max. | Unit |
|----------------------|-----------------|-----------------------|------|-----|------|------|
| Total gate charge | Q _g | V _{DD} = 25V | - | 12 | - | nC |
| Gate - Source charge | Q _{gs} | I _D = 8A | - | 4 | - | |
| Gate - Drain charge | Q _{gd} | V _{GS} = 10V | - | 6 | - | |

Note: ① Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2% ;

② Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate;

Fig.1 Power Dissipation Derating Curve

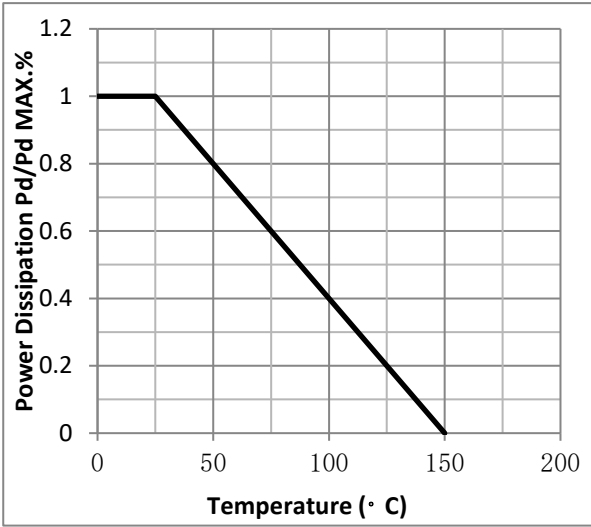


Fig.2 Typical output Characteristics

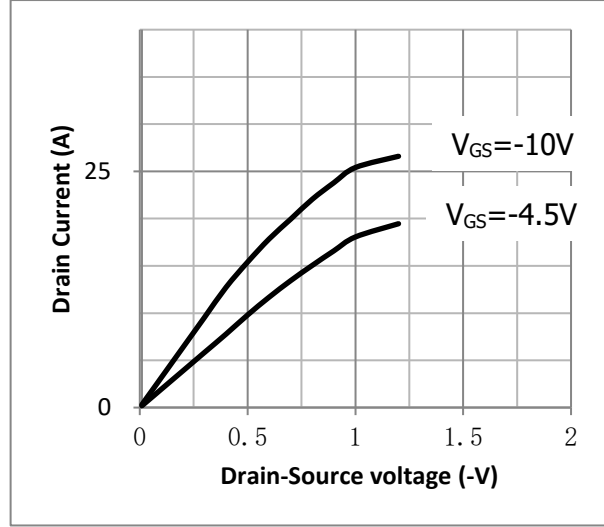


Fig.3 Threshold Voltage V.S Junction Temperature

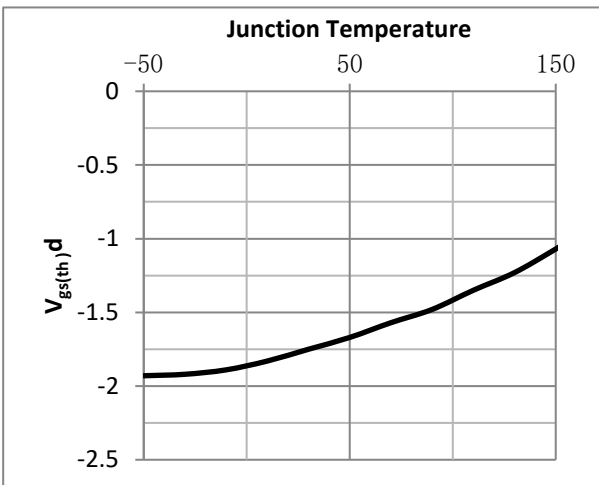


Fig.4 Resistance V.S Drain Current

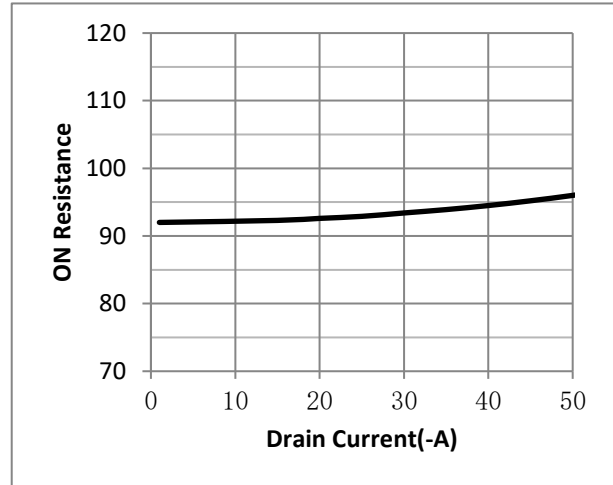


Fig.5 On-Resistance VS Gate Source Voltage

Fig.6 On-Resistance V.S Junction Temperature

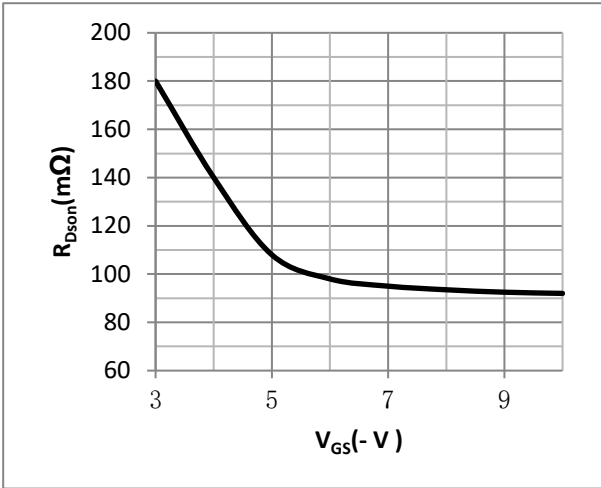


Fig.7 Switching Time Measurement Circuit

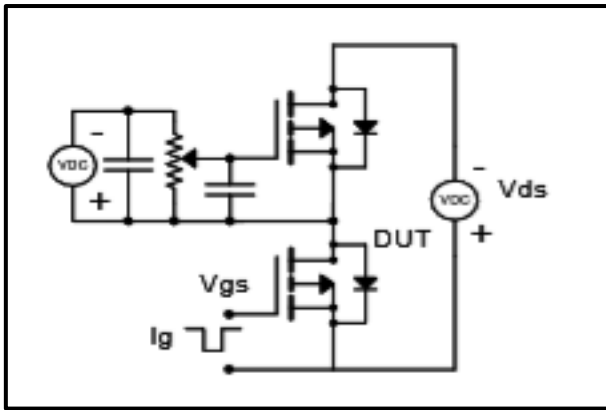


Fig.9 Switching Time Measurement Circuit

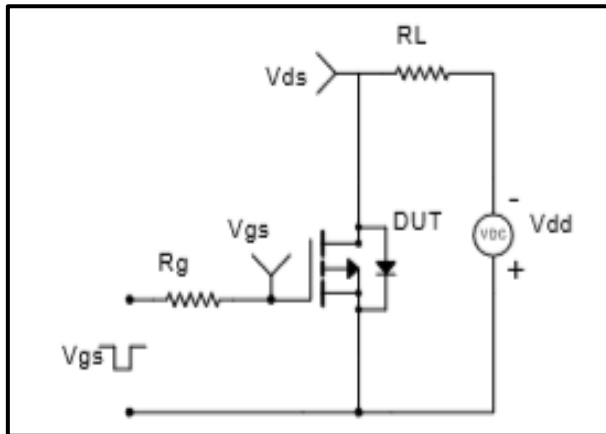


Fig.11 Avalanche Measurement Circuit

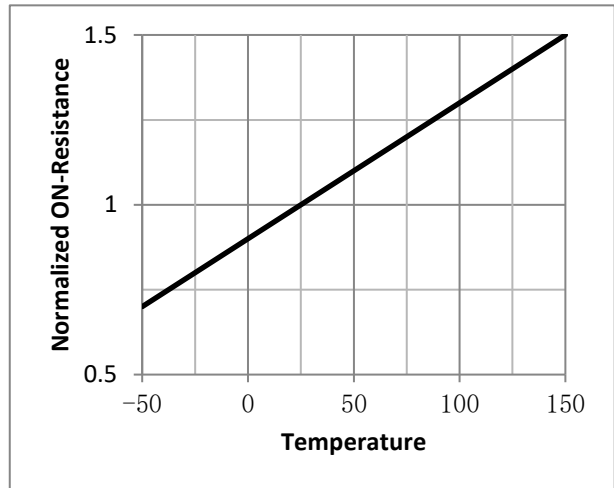
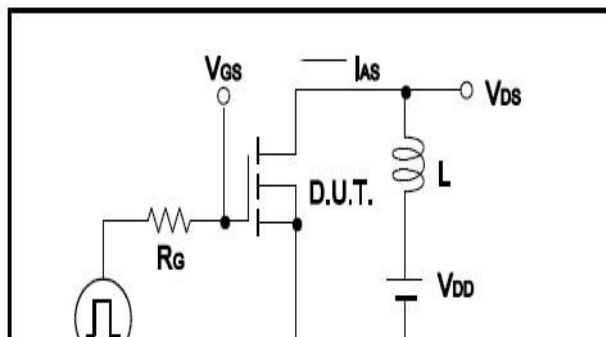


Fig.8 Gate Charge Waveform

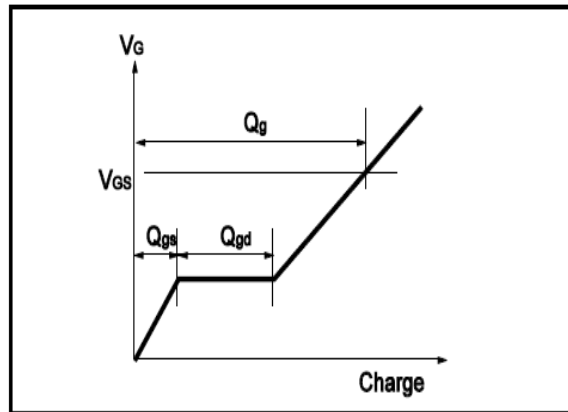


Fig.10 Gate Charge Waveform

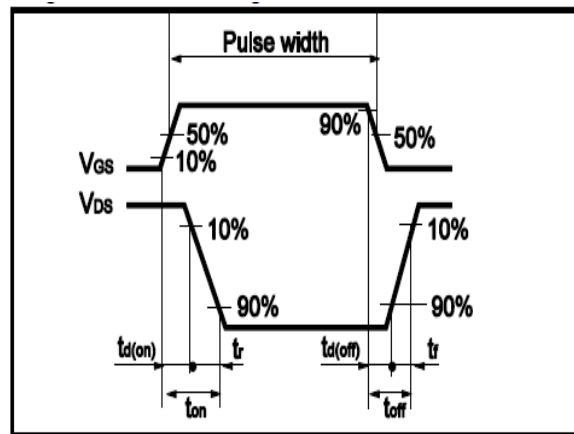
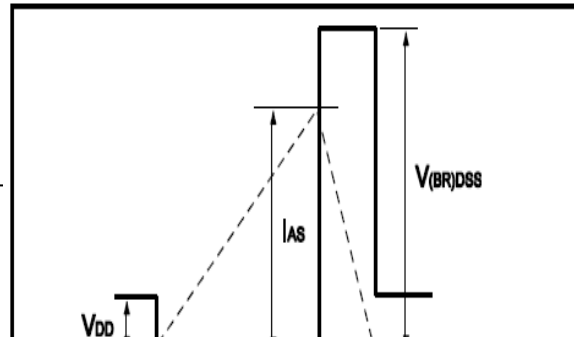
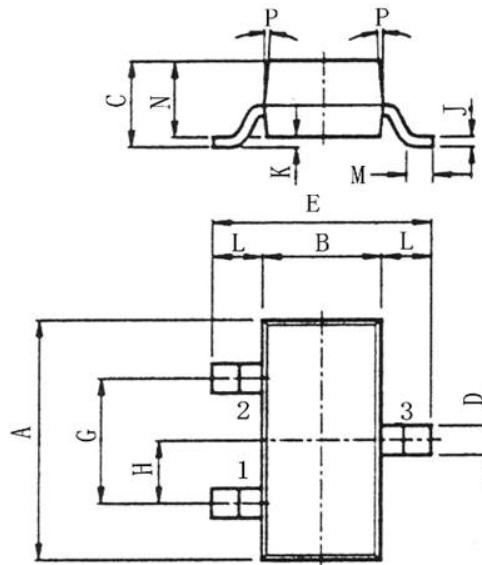


Fig.12 Avalanche Waveform



•Dimensions(SOT23)

Unit: mm



| SYMBOL | min | nom | max |
|--------|------|------|------|
| A | 2.70 | 2.9 | 3.10 |
| B | 1.15 | 1.3 | 1.50 |
| C | | | 1.30 |
| D | 0.35 | 0.4 | 0.55 |
| E | 2.20 | 2.4 | 2.70 |
| G | 1.70 | 1.9 | 2.10 |
| H | 0.85 | 0.95 | 1.05 |
| J | 0.05 | 0.10 | 0.20 |
| K | 0.00 | | 0.10 |



| | | | |
|---|------|------|------|
| L | 0.45 | 0.55 | 0.65 |
| M | 0.20 | | |
| N | 0.90 | 1.00 | 1.20 |
| P | | 7° | |